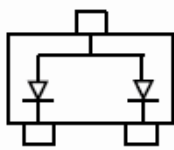


SCHOTTKY DIODES

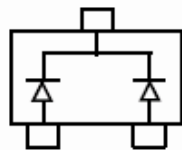
FEATURES

- Fast Switching Speed
- For General Purpose Switching Applications
- High Conductance

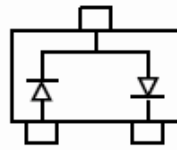
MARKING:



BAW56:A1



BAV70:A4



BAV99:A7

BAW56/BAV70/BAV99



MAXIMUM RATINGS (TA=25°C unless otherwise noted)

Parameter	Symbol	Limit	Unit
Reverse voltage	V	70	V
Forward Current	I	200	mA
Peak Forward Surge Current	IFM(surge)	500	mA
Power Dissipation	P	225	mW
Thermal Resistance Junction to Ambient Air	R J	556	°C/W
Junction temperature	T	150	°C
Storage temperature range	TST	-55-150	°C

ELECTRICAL CHARACTERISTICS (Tamb=25°C unless otherwise specified)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Reverse Breakdown Voltage	V R	70			V	IR=100µA
Forward voltage	VF1			0.715	V	IF=1mA
	VF2			0.855	V	IF=10mA
	VF3			1	V	IF=50mA
	VF4			1.25	V	IF=150mA
Reverse current	IR			2.5	µA	VR=70V
Capacitance between terminals	CT			1.5	pF	VR=0,f=1MHz
Reverse recovery time	t <sub>rr</sub>			6	ns	IF = IR = 10mA, Irr= 0.1 x IR, RL = 100

**BAW56/BAV70/BAV99** Typical Characteristics

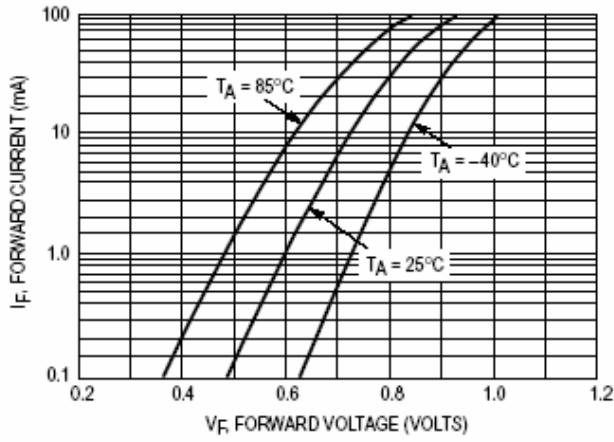


Figure 1. Forward Voltage

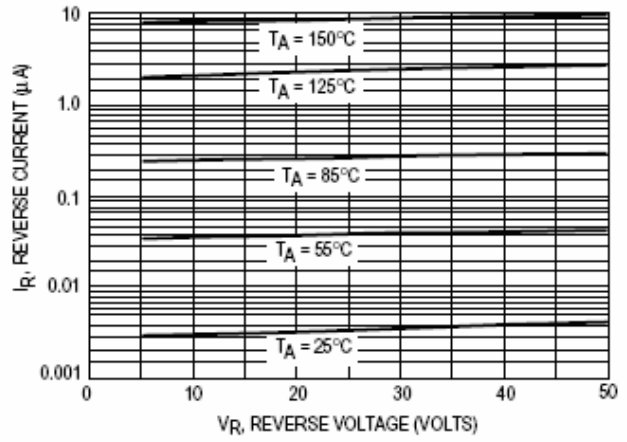


Figure 2 Leakage Current

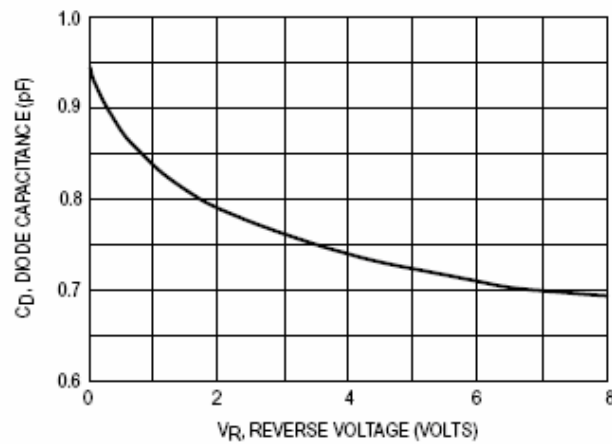


Figure 3 Capacitance